



PATENT APPLICATION  
Do. No. 5484-093

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Byeong-Hoon LEE and Seung-Keun LEE

Serial No. 09/997,080

Examiner: Phan, Trong Q

Filed: November 28, 2001

Group Art Unit: 2818

For: NONVOLATILE SEMICONDUCTOR MEMORY DEVICE

Confirmation No. 6095

BOX RCE  
Assistant Commissioner for Patents  
Washington, D.C. 20231

### REQUEST FOR CONTINUED EXAMINATION

Responsive to the Final Office Action mailed November 14, 2002, and the Advisory Action, mailed January 29, 2003, please amend the application as follows.

### IN THE CLAIMS

Please replace the claims with the following set, in which claims 1, 10, 15, and 18 are amended and claims 26 and 27 are new.

- sub*  
*D1*
1. (Amended) A nonvolatile semiconductor memory device comprising:  
a substrate;  
a plurality of sectors on the substrate;  
each sector comprising memory cell transistors arranged in a cell array block and decoder transistors in a column decoder block;  
*cl*  
wherein the transistors in the cell array block and column decoder block in each sector share a common bulk region, wherein the common bulk region is formed on the substrate and is connected to a bulk driver provided in each of the sectors, each said bulk driver configured to commonly apply a bulk voltage to the common bulk region of the sector; and  
wherein said semiconductor memory device is configured to electrically erase all the memory cell transistors in a sector together.

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3/26/03